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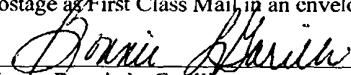
Docket No. 740819-442

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
Akihiko ISHIBASHI et al.) Examiner: Savitri Mulpuri
Serial No. 09/692,211)
Filed: October 20, 2000) Group Art Unit: 2812
For: METHOD OF FABRICATING NITRIDE SEMI-) Confirmation No.: 6705
CONDUCTOR DEVICE)

Certificate of Mailing

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Name: Bonnie L. Garilli

REQUEST FOR ACKNOWLEDGMENT OF
INFORMATION DISCLOSURE STATEMENT

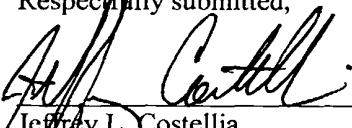
Commissioner for Patents
Washington, D.C. 20231

Sir:

An Information Disclosure Statement with Form PTO-1449 was filed in the above-identified patent application on September 19, 2002. Applicants have received back from the Examiner a partially considered copy of the Form PTO-1449 initialed to acknowledge the fact that the Examiner has considered the cited disclosed information.

The Examiner is requested to initial and return to the undersigned a copy of the subject Form PTO-1449.

Should there be any questions concerning this communication, please telephone the undersigned at the number set forth below.

Respectfully submitted,

Jeffrey L. Costellia
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U.S. Department of Commerce
Patent and Trademark Office

Atty Docket 740819-442

Serial No. 09/692,211

Applicants: Akihiko ISHIBASHI et al.

Filing Date: October 20, 2000

Group Art Unit: 2812

INFORMATION DISCLOSURE STATEMENT

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
	5,787,104	07/28/1998	Kamiyama et al.			

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Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
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	08-255932	10/01/1996	JP				X
	08-316141	11/29/1996	JP			Part Eng	
	09-213998	08/15/1997	JP			Part Eng	
	10-182282	07/07/1998	JP			Part Eng	
	11-074203	03/16/1999	JP			Part Eng	
	2702889	10/03/1997	JP				X

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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gm	Miyake et al., "Effects of Reactor Pressure on Epitaxial Lateral Overgrowth of GaN via Low-Pressure Metalorganic Vapor Phase Epitaxy", pp. L1000-L1002, September 15, 1999, Jpn. J. Appl. Phys., Vol 38, Part 2, No. 9A/B
	Nakamura et al., "AlN and AlGaIn Growth Using Low-Pressure Metalorganic Chemical Vapor Deposition", pp. 280-285, 1998, Journal of Crystal Growth 195
	Mihopoulos, et al., "A Reaction-Transport Model for AlGaIn MOVPE Growth", pp. 733-739, 1998, Journal of Crystal Growth 195
	Lee et al., "Characteristics of In Ga N/GaN Grown by LPMOVPE with the Variation of Growth Temperature", pp. 6-10, 1997, Journal of Crystal Growth 182

Examiner

Date Considered

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

09/19/2002